

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	298	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 10:18
S2	295	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 20:08
S3	264	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 10:20
S4	215	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:18

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S5	1	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and (onium near8 compound) and nucleophil\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 10:45
S6	1	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and (onium near8 compound)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 10:46

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S7	21	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 11:14
S8	0	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and catalyst and porogen and (heat or anneal) and gell	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 11:17

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S9	21	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 11:18
S11	2	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal) and (remov\$4 near8 porogen) and onium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/16 11:19

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S12	21	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and solvent and polymer and catalyst and porogen and (heat or anneal) and (remov\$4 near8 porogen)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 11:49
S13	124	"5895263"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 11:49
S14	76	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:21

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S15	28	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4 and catalyst	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:22
S16	1	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and ("nanoporous silica" or "silicon oxide" or "organosilesquioxane" or "polysiloxane" or "polyaryleneether" or "polyimide") and ("SiC" or "silicon carbide" or "silicon oxide" or "SiN" or "silicon nitride" or "silicon oxynitride" or tungsten or "WN" or "tungsten nitride" or "Ta" or tantalum or "TaN" or "tantalum nitride" or "Ti" or titanium or "TiN" or "titanium nitride" or "titanium zirconium nitride") and gel\$4 and catalyst and onium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:23
S17	1	(porous near4 dielectric) and (adhesion near8 dielectric) and (cap\$4 near4 layer) and poro\$4 and (substrate or semiconductor or wafer) and "dielectric constant" and gel\$4 and catalyst and onium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:24
S18	4601	gel\$4 and catalyst and onium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:24

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S19	1348	gel\$4 and catalyst and (onium near4 compound)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:25
S20	46	gel\$4 and catalyst and (onium near4 compound) and nucleophile	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:31
S22	5	gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene and (acetoxysilane or ethoxysilane or methoxysilane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:34
S23	1	gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene and (acetoxysilane or ethoxysilane or methoxysilane) and infiltrat\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/17 12:33
S24	11	gel\$4 and catalyst and (onium near4 compound) and nucleophile and polyalkylene	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 08:06
S25	55165	(porous near9 (dielectric or oxide or insulat\$4))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 20:26
S26	9916	(porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 21:03

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S27	0	(porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near cap)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 21:29
S28	22	(porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near (oxide or dielectric or insulat\$4 or cap))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 21:29
S29	20	(porous near9 (dielectric or oxide or insulat\$4)) and ((silicon near oxide) or polyimide) and (nonporous near (oxide or dielectric or insulat\$4 or cap)) and (substrate or wafer or carrier or base)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/23 21:31